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REMARKS

The claims are now 1-2 and 4-13.

The amended claims and specification paragraph are set forth above. Attached hereto is an Appendix showing the amendments by bracketing matter to be deleted and underlining matter to be added.

Claims 1-9 have been rejected under 35 USC 102(e) as anticipated by, or, in the alternative, under 35 USC 103(a) as obvious over Khan et al. These rejections are respectfully traversed in view of the amendments to the claims.

Applicants found that when the bias power to the substrate support is pulsed during etching and overetching, notching is reduced.

Khan et al also describe notching when etching silicon with an anisotropic etchant, but no pulsing of the bias power is described or suggested. Khan et al's answer to the notching problem is to etch with an anisotropic etch rapidly, and complete the etching step by using an HBr/oxygen etchant, which deposits a protective sidewall layer to prevent isotropic etching, or notching, at the bottom of the etched feature.

Thus applicants submit Khan et al neither anticipate the

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claims as amended, which requires pulsed bias power to eliminate notching, nor render the present claims obvious; Khan et al do disclose the notching problem, but try to solve it in an entirely different way. No pulsing of the bias power is suggested in Khan et al at all.

Since all of the present claims require pulsing the bias power to reduce or eliminate notching, applicants submit the present claims are neither anticipated by, nor obvious over, Khan et al.

The additional references cited by the Examiner have not been used to reject the claims.

If the Examiner believes a telephone interview would advance the prosecution of this application, he/she is invited to contact the undersigned.

In view of the above amendments and discussion, applicants submit that the present claims are patentable over the art of record. Accordingly, reconsideration and allowance of the claims as amended are respectfully solicited.

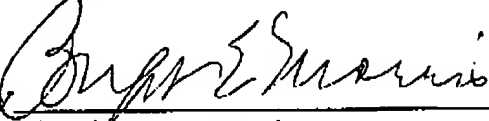
This amendment is accompanied by a Petition to Revive and a

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Petition fee charged to a Deposit Account.

Respectfully submitted,

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APPENDIX

COPY OF AMENDMENT TO THE SPECIFICATION WITH CHANGES SHOWN

Paragraph beginning on page 9 line 14:

In this Example, no bias power was used during the deposition steps, but 30 Watts of pulsed bias power was used during the etch steps, again using a duty cycle of 35% and a [periof] period of 6 milliseconds. The average power delivered was 6 Watts.

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COPY OF AMENDMENTS TO THE CLAIMS WITH CHANGES SHOWN

1 (Amended). A method of reducing notching in etched anisotropic openings in silicon over an insulator layer comprising

anisotropically etching openings in silicon with a sulfur hexafluoride etchant in a plasma etch chamber fitted with a powered substrate support while pulsed bias power is applied to the substrate support electrode during the etch step.

4 (Amended). A method according to claim [3] 2 wherein the pulsed bias power is applied at a duty cycle of 10% to 80% using a 6 microsecond period.